

Fang-Fang Ren

List of Publications by Year in descending order

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186265

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docs citations

134
times ranked

2733
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#	ARTICLE	IF	CITATIONS
1	Review of gallium-oxide-based solar-blind ultraviolet photodetectors. <i>Photonics Research</i> , 2019, 7, 381.	7.0	391
2	Solar-Blind Photodetector with High Avalanche Gains and Bias-Tunable Detecting Functionality Based on Metastable Phase $\text{In}_2\text{Ga}_2\text{O}_3/\text{ZnO}$ Isotype Heterostructures. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 36997-37005.	8.0	158
3	A 1.86-kV double-layered $\text{NiO}/\text{In}_2\text{O}_3$ vertical p-n heterojunction diode. <i>Applied Physics Letters</i> , 2020, 117, .	3.3	136
4	Electrical instability of amorphous indium-gallium-zinc oxide thin film transistors under monochromatic light illumination. <i>Applied Physics Letters</i> , 2012, 100, 243505.	3.3	82
5	Split Bullseye Shaped Aluminum Antenna for Plasmon-Enhanced Nanometer Scale Germanium Photodetector. <i>Nano Letters</i> , 2011, 11, 1289-1293.	9.1	80
6	1.37 kV/12 A $\text{NiO}/\text{In}_2\text{Ga}_2\text{O}_3$ Heterojunction Diode With Nanosecond Reverse Recovery and Rugged Surge-Current Capability. <i>IEEE Transactions on Power Electronics</i> , 2021, 36, 12213-12217.	7.9	77
7	Controllable electromagnetic transmission based on dual-metallic grating structures composed of subwavelength slits. <i>Applied Physics Letters</i> , 2007, 91, 111111.	3.3	75
8	Gallium oxide-based solar-blind ultraviolet photodetectors. <i>Semiconductor Science and Technology</i> , 2020, 35, 023001.	2.0	73
9	Giant enhancement of second harmonic generation in a finite photonic crystal with a single defect and dual-localized modes. <i>Physical Review B</i> , 2004, 70, .	3.2	69
10	Physical mechanism of extraordinary electromagnetic transmission in dual-metallic grating structures. <i>Physical Review B</i> , 2008, 78, .	3.2	68
11	Hybridized surface plasmon polaritons at an interface between a metal and a uniaxial crystal. <i>Applied Physics Letters</i> , 2008, 92, 141115.	3.3	67
12	$\text{In}_2\text{Ga}_2\text{O}_3$ vertical heterojunction barrier Schottky diodes terminated with p-NiO field limiting rings. <i>Applied Physics Letters</i> , 2021, 118, .	3.3	65
13	Band Alignment and Interface Recombination in $\text{NiO}/\text{In}_2\text{Ga}_2\text{O}_3$ Type-II p-n Heterojunctions. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 3341-3347.	3.0	63
14	Carrier Transport and Gain Mechanisms in $\text{In}_2\text{Ga}_2\text{O}_3$ -Based Metal-Semiconductor-Metal Solar-Blind Schottky Photodetectors. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 2276-2281.	3.0	59
15	Enhanced bias stress stability of a-InGaZnO thin film transistors by inserting an ultra-thin interfacial InGaZnO:N layer. <i>Applied Physics Letters</i> , 2013, 102, .	3.3	57
16	Highly Narrow-Band Polarization-Sensitive Solar-Blind Photodetectors Based on $\text{In}_2\text{Ga}_2\text{O}_3$ Single Crystals. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 7131-7137.	8.0	55
17	High-Temperature Single Photon Detection Performance of 4H-SiC Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , 2014, 26, 1136-1138.	2.5	53
18	Raman-active $\text{A}_1(\text{TO})$ optical phonon mode in arsenic implanted ZnO. <i>Applied Physics Letters</i> , 2009, 94, 011913.	3.3	49

#	ARTICLE	IF	CITATIONS
19	High Quantum Efficiency GaN-Based p-i-n Ultraviolet Photodetectors Prepared on Patterned Sapphire Substrates. IEEE Photonics Technology Letters, 2013, 25, 652-654.	2.5	45
20	Heteroepitaxial growth of thick Ga_2O_3 film on sapphire (0001) by MIST-CVD technique. Journal of Semiconductors, 2019, 40, 012804.	3.7	45
21	Identification and modulation of electronic band structures of single-phase $\text{In}^{2-}(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3$ alloys grown by laser molecular beam epitaxy. Applied Physics Letters, 2018, 113, .	3.3	43
22	Surface plasmon enhanced responsivity in a waveguided germanium metal-semiconductor-metal photodetector. Applied Physics Letters, 2010, 97, .	3.3	40
23	On the origin of dislocation generation and annihilation in In^{2-} -Ga $_2\text{O}_3$ epilayers on sapphire. Applied Physics Letters, 2019, 115, .	3.3	37
24	Magnesium ion-implantation-based gallium nitride p-i-n photodiode for visible-blind ultraviolet detection. Photonics Research, 2019, 7, B48.	7.0	36
25	Hybrid Light Emitters and UV Solar-Blind Avalanche Photodiodes based on III-Nitride Semiconductors. Advanced Materials, 2020, 32, e1904354.	21.0	34
26	Vertically Emitting Indium Phosphide Nanowire Lasers. Nano Letters, 2018, 18, 3414-3420.	9.1	33
27	Large-Swing a-IGZO Inverter With a Depletion Load Induced by Laser Annealing. IEEE Electron Device Letters, 2014, 35, 1034-1036.	3.9	30
28	Large-scale fabrication and luminescence properties of GaN nanostructures by a soft UV-curing nanoimprint lithography. Nanotechnology, 2013, 24, 405303.	2.6	29
29	High-Voltage Quasi-Vertical GaN Junction Barrier Schottky Diode With Fast Switching Characteristics. IEEE Electron Device Letters, 2021, 42, 974-977.	3.9	29
30	High-Brightness Polarized Green InGaN/GaN Light-Emitting Diode Structure with Al-Coated p-GaN Grating. ACS Photonics, 2016, 3, 1912-1918.	6.6	28
31	Phase tailoring and wafer-scale uniform hetero-epitaxy of metastable-phased corundum In^{2-} -Ga $_2\text{O}_3$ on sapphire. Applied Surface Science, 2020, 513, 145871.	6.1	28
32	Transition of photoconductive and photovoltaic operation modes in amorphous Ga_2O_3 -based solar-blind detectors tuned by oxygen vacancies. Chinese Physics B, 2019, 28, 028501.	1.4	26
33	Band alignment and band bending at In^{2-} -Ga $_2\text{O}_3$ /ZnO n-n isotype hetero-interface. Applied Physics Letters, 2019, 115, .	3.3	25
34	Realization of p-type gallium nitride by magnesium ion implantation for vertical power devices. Scientific Reports, 2019, 9, 8796.	3.3	24
35	In situ heteroepitaxial construction and transport properties of lattice-matched In^{2-} -Ir $_2\text{O}_3$ / In^{2-} -Ga $_2\text{O}_3$ p-n heterojunction. Applied Physics Letters, 2021, 118, .	3.3	24
36	Over 1.8 GW/cm 2 beveled-mesa NiO/ In^{2-} -Ga $_2\text{O}_3$ heterojunction diode with 800 V/10 A nanosecond switching capability. Applied Physics Letters, 2021, 119, .	3.3	24

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37	Manipulable and Hybridized, Ultralow-Threshold Lasing in a Plasmonic Laser Using Elliptical InGaN/GaN Nanorods. <i>Advanced Functional Materials</i> , 2017, 27, 1703198.	14.9	23
38	Majority and Minority Carrier Traps in NiO/ Ga_2O_3 p ⁺ -n Heterojunction Diode. <i>IEEE Transactions on Electron Devices</i> , 2022, 69, 981-987.	3.0	23
39	Fast Speed Ga ₂ O ₃ Solar-blind Schottky Photodiodes with Large Sensitive Area. <i>IEEE Electron Device Letters</i> , 2020, , 1-1.	3.9	22
40	Electrically tunable terahertz metamaterials with embedded large-area transparent thin-film transistor arrays. <i>Scientific Reports</i> , 2016, 6, 23486.	3.3	21
41	4H-SiC p-i-n Ultraviolet Avalanche Photodiodes Obtained by Al Implantation. <i>IEEE Photonics Technology Letters</i> , 2016, 28, 1185-1188.	2.5	20
42	High- k HfO ₂ -Based AlGaIn/GaN MIS-HEMTs With Y ₂ O ₃ Interfacial Layer for High Gate Controllability and Interface Quality. <i>IEEE Journal of the Electron Devices Society</i> , 2020, 8, 15-19.	2.1	19
43	Demonstration of Avalanche and Surge Current Robustness in GaN Junction Barrier Schottky Diode With 600-V/10-A Switching Capability. <i>IEEE Transactions on Power Electronics</i> , 2021, 36, 12163-12167.	7.9	19
44	70- μm -Body Ga ₂ O ₃ Schottky Barrier Diode With 1.48 K/W Thermal Resistance, 59 A Surge Current and 98.9% Conversion Efficiency. <i>IEEE Electron Device Letters</i> , 2022, 43, 773-776.	3.9	19
45	High Quantum Efficiency Back-Illuminated AlGaIn-Based Solar-Blind Ultraviolet p ⁺ -n Photodetectors. <i>Chinese Physics Letters</i> , 2012, 29, 097302.	3.3	18
46	Temperature and gate bias dependence of carrier transport mechanisms in amorphous indium-gallium-zinc oxide thin film transistors. <i>Solid-State Electronics</i> , 2013, 86, 41-44.	1.4	18
47	Anion Engineering Enhanced Response Speed and Tunable Spectral Responsivity in Gallium-Oxynitrides-Based Ultraviolet Photodetectors. <i>ACS Applied Electronic Materials</i> , 2020, 2, 808-816.	4.3	18
48	1.2 kV/25 A Normally off P-N Junction/AlGaIn/GaN HEMTs With Nanosecond Switching Characteristics and Robust Overvoltage Capability. <i>IEEE Transactions on Power Electronics</i> , 2022, 37, 26-30.	7.9	18
49	Bias stress instability involving subgap state transitions in a-IGZO Schottky barrier diodes. <i>Journal Physics D: Applied Physics</i> , 2016, 49, 395104.	2.8	16
50	Single nanowire green InGaIn/GaN light emitting diodes. <i>Nanotechnology</i> , 2016, 27, 435205.	2.6	16
51	High Fill-Factor 4H-SiC Avalanche Photodiodes With Partial Trench Isolation. <i>IEEE Photonics Technology Letters</i> , 2016, 28, 2526-2528.	2.5	16
52	High-Performance 4H-SiC p-i-n Ultraviolet Photodiode With p Layer Formed by Al Implantation. <i>IEEE Photonics Technology Letters</i> , 2016, 28, 1189-1192.	2.5	16
53	Analysis of Dark Count Mechanisms of 4H-SiC Ultraviolet Avalanche Photodiodes Working in Geiger Mode. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 4532-4539.	3.0	16
54	Highly Enhanced Inductive Current Sustaining Capability and Avalanche Ruggedness in GaN p-i-n Diodes With Shallow Bevel Termination. <i>IEEE Electron Device Letters</i> , 2020, 41, 469-472.	3.9	16

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55	Second-order surface-plasmon assisted responsivity enhancement in germanium nano-photodetectors with bullâ€™s eye antennas. Optics Express, 2014, 22, 15949.	3.4	15
56	4H-SiC SACM Avalanche Photodiode With Low Breakdown Voltage and High UV Detection Efficiency. IEEE Photonics Journal, 2016, 8, 1-7.	2.0	15
57	A Terahertz Controlledâ€™NOT Gate Based on Asymmetric Rotation of Polarization in Chiral Metamaterials. Advanced Optical Materials, 2017, 5, 1700108.	7.3	15
58	Band Alignment and Enhanced Interfacial Conductivity Manipulated by Polarization in a Surfactant-Mediated Grown $\text{In}_2\text{O}_3/\text{Ga}_2\text{O}_3$ Heterostructure. ACS Applied Electronic Materials, 2021, 3, 795-803.	4.3	15
59	High-temperature and reliability performance of 4H-SiC Schottky-barrier photodiodes for UV detection. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2015, 33, .	1.2	14
60	A self-powered solar-blind photodetector based on polyaniline/ In_2O_3 heterojunction. Applied Physics Letters, 2021, 119, .	3.3	14
61	4H-SiC Avalanche Photodiode Linear Array Operating in Geiger Mode. IEEE Photonics Journal, 2017, 9, 1-7.	2.0	13
62	Extreme absorption enhancement in ZnTe:O/ZnO intermediate band core-shell nanowires by interplay of dielectric resonance and plasmonic bowtie nanoantennas. Scientific Reports, 2017, 7, 7503.	3.3	12
63	Passive Quenching Electronics for Geiger Mode 4H-SiC Avalanche Photodiodes. Chinese Physics Letters, 2015, 32, 128501.	3.3	11
64	M-Plane In_2O_3 Solar-Blind Detector With Record-High Responsivity-Bandwidth Product and High-Temperature Operation Capability. IEEE Electron Device Letters, 2022, 43, 541-544.	3.9	11
65	Temperature-dependent efficiency droop behaviors of GaN-based green light-emitting diodes. Chinese Physics B, 2013, 22, 047805.	1.4	10
66	Investigation of surface-plasmon coupled red light emitting InGaN/GaN multi-quantum well with Ag nanostructures coated on GaN surface. Journal of Applied Physics, 2015, 117, .	2.5	10
67	Distinct enhancement of sub-bandgap photoresponse through intermediate band in high dose implanted ZnTe:O alloys. Scientific Reports, 2017, 7, 44399.	3.3	10
68	Single Photon Counting Spatial Uniformity of 4H-SiC APD Characterized by SNOM-Based Mapping System. IEEE Photonics Technology Letters, 2017, 29, 1603-1606.	2.5	10
69	Effect of Very High-Fluence Proton Radiation on 6H-SiC Photoconductive Proton Detectors. IEEE Electron Device Letters, 2019, 40, 1929-1932.	3.9	10
70	Electron-Beam-Driven III-Nitride Plasmonic Nanolasers in the Deep-UV and Visible Region. Small, 2020, 16, 1906205.	10.0	10
71	High-Performance 4H-SiC Schottky Photodiode With Semitransparent Grid-Electrode for EUV Detection. IEEE Photonics Technology Letters, 2020, 32, 791-794.	2.5	10
72	Field-Plated NiO/ Ga_2O_3 p-n Heterojunction Power Diodes With High-Temperature Thermal Stability and Near Unity Ideality Factors. IEEE Journal of the Electron Devices Society, 2021, 9, 1166-1171.	2.1	10

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73	Strong vertical light output from thin silicon rich oxide/SiO ₂ multilayers via in-plane modulation of photonic crystal patterns. Applied Physics Letters, 2008, 93, 091901.	3.3	9
74	Raman probing of competitive laser heating and local recrystallization effect in ZnO nanocrystals. Optics Express, 2012, 20, 23281.	3.4	9
75	High Deep-Ultraviolet Quantum Efficiency GaN Pê”îê”N Photodetectors with Thin P-GaN Contact Layer. Chinese Physics Letters, 2013, 30, 017302.	3.3	9
76	Demonstration of an AlGaN-based solar-blind high-voltage photoconductive switch. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2015, 33, 040601.	1.2	9
77	Split Bullâ€™s Eye Antenna for High-Speed Photodetector in the Range of Visible to Mid-Infrared. IEEE Photonics Technology Letters, 2016, 28, 1177-1180.	2.5	9
78	Vertical 4H-SiC n-i-p-n APDs With Partial Trench Isolation. IEEE Photonics Technology Letters, 2018, 30, 805-808.	2.5	9
79	Investigations of the gate instability characteristics in Schottky/ohmic type p-GaN gate normally-off AlGaN/GaN HEMTs. Applied Physics Express, 2019, 12, 121005.	2.4	9
80	Gate-first process compatible, high-quality <i>in situ</i> SiN_x for surface passivation and gate dielectrics in AlGaN/GaN MISHEMTs. Journal Physics D: Applied Physics, 2019, 52, 305105.	2.8	9
81	Polarizationâ€”Independent Indium Phosphide Nanowire Photodetectors. Advanced Optical Materials, 2020, 8, 2000514.	7.3	9
82	Electromagnetic transmission through one-dimensional gratings with left-handed materials. Physical Review B, 2007, 75, .	3.2	8
83	Frequency Performance of Ring Oscillators Based on a-IGZO Thin-Film Transistors. Chinese Physics Letters, 2015, 32, 047302.	3.3	8
84	Study on interface characteristics in amorphous indiumâ€”galliumâ€”zinc oxide thin-film transistors by using low-frequency noise and temperature dependent mobility measurements. Solid-State Electronics, 2015, 109, 37-41.	1.4	8
85	4H-SiC Ultraviolet Avalanche Photodiodes With Small Gain Slope and Enhanced Fill Factor. IEEE Photonics Journal, 2017, 9, 1-8.	2.0	8
86	Tailored Emission Properties of ZnTe/ZnTe:O/ZnO Coreâ€”Shell Nanowires Coupled with an Al Plasmonic Bowtie Antenna Array. ACS Nano, 2018, 12, 7327-7334.	14.6	8
87	Unlocking the Single-Domain Heteroepitaxy of Orthorhombic Î”-Ga₂O₃ via Phase Engineering. ACS Applied Electronic Materials, 2022, 4, 461-468.	4.3	8
88	Band alignment and polarization engineering in Î”-Ga ₂ O ₃ /GaN ferroelectric heterojunction. Science China: Physics, Mechanics and Astronomy, 2022, 65, .	5.1	8
89	Bias-Selective Dual-Operation-Mode Ultraviolet Schottky-Barrier Photodetectors Fabricated on High-Resistivity Homoepitaxial GaN. IEEE Photonics Technology Letters, 2012, 24, 2203-2205.	2.5	7
90	Solar-blind ultraviolet band-pass filter based on metalâ€”dielectric multilayer structures. Chinese Physics B, 2014, 23, 074201.	1.4	7

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91	High-voltage photoconductive semiconductor switches fabricated on semi-insulating HVPE GaN:Fe template. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016, 13, 374-377.	0.8	7
92	Avalanche Ruggedness of GaN p-i-n Diodes Grown on Sapphire Substrate. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1800069.	1.8	7
93	Metal-semiconductor-metal ultraviolet photodetectors directly fabricated on semi-insulating GaN:Fe template grown by hydride vapor phase epitaxy. <i>Sensors and Actuators A: Physical</i> , 2014, 216, 308-311.	4.1	6
94	Bloch surface plasmon enhanced blue emission from InGaN/GaN light-emitting diode structures with Al-coated GaN nanorods. <i>Nanotechnology</i> , 2015, 26, 125201.	2.6	6
95	Spatial Non-Uniform Hot Carrier Luminescence From 4H-SiC p-i-n Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , 2019, 31, 447-450.	2.5	6
96	Vertical Field-Plated NiO/Ga ₂ O ₃ Heterojunction Power Diodes. , 2021, , .		6
97	High Performance Quasi-Vertical GaN Junction Barrier Schottky Diode with Zero Reverse Recovery and Rugged Avalanche Capability. , 2021, , .		6
98	Low-threshold and high-efficiency optical parametric oscillator using a one-dimensional single-defect photonic crystal with quadratic nonlinearity. <i>Physical Review B</i> , 2006, 73, .	3.2	5
99	Second-harmonic generation in photonic crystals with a pair of epsilon-negative and mu-negative defects. <i>Optics Express</i> , 2009, 17, 6682.	3.4	5
100	Enhanced Vertical Light Extraction From Ultrathin Amorphous Si ₃ N ₄ Multilayers With Photonic Crystal Patterns. <i>IEEE Photonics Technology Letters</i> , 2009, 21, 91-93.	2.5	5
101	After-Pulse Characterizations of Geiger-Mode 4H-SiC Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , 2020, 32, 706-709.	2.5	5
102	Property manipulation through pulsed laser annealing in high dose Mg-implanted GaN. <i>Journal of Applied Physics</i> , 2020, 128, .	2.5	5
103	Dislocation dynamics in \pm -Ga ₂ O ₃ micropillars from selective-area epitaxy to epitaxial lateral overgrowth. <i>Applied Physics Letters</i> , 2022, 120, .	3.3	5
104	Dual localizations for second-harmonic generations using left-handed materials. <i>Applied Physics Letters</i> , 2005, 87, 251104.	3.3	4
105	Temperature-dependent bias-stress-induced electrical instability of amorphous indium-gallium-zinc-oxide thin-film transistors. <i>Chinese Physics B</i> , 2015, 24, 077307.	1.4	4
106	Boosting Hot-Electron Extraction Through Deep Groove Perfect Absorber for Si-Based Photodetector. <i>IEEE Photonics Technology Letters</i> , 2017, 29, 1884-1887.	2.5	4
107	Crosstalk Analysis of SiC Ultraviolet Single Photon Avalanche Photodiode Arrays. <i>IEEE Photonics Journal</i> , 2019, 11, 1-8.	2.0	4
108	Misfit epitaxial strain manipulated transport properties in cubic In ₂ O ₃ hetero-epilayers. <i>Applied Physics Letters</i> , 2020, 117, 102104.	3.3	4

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109	1000-W Resistive Energy Dissipating Capability Against Inductive Transients Demonstrated in Non-Avalanche AlGaIn/GaN Schottky Diode. IEEE Electron Device Letters, 2021, 42, 1743-1746.	3.9	4
110	Saturation effect and forward-dominant second-harmonic generation in single-defect photonic crystals with dual localizations. Optics Letters, 2006, 31, 3327.	3.3	3
111	Off-state breakdown and leakage current transport analysis of AlGaIn/GaN high electron mobility transistors. Microelectronics Reliability, 2014, 54, 2406-2409.	1.7	3
112	Low-threshold ultraviolet stimulated emissions from large-sized single crystalline ZnO transferable membranes. Optics Express, 2018, 26, 31965.	3.4	3
113	Investigation and active suppression of self-heating induced degradation in amorphous InGaZnO thin film transistors. Chinese Physics B, 2019, 28, 017303.	1.4	3
114	Nanometer germanium photodetector with aluminum surface plasmon antenna for enhanced photo-response. , 2010, , .		2
115	Spectrum broadening of high-efficiency second harmonic generation in cascaded photonic crystal microcavities. Optics Express, 2013, 21, 756.	3.4	2
116	Vacuum Violet Photo-Response of AlGaIn-Based Metal-Semiconductor-Metal Photodetectors. Chinese Physics Letters, 2013, 30, 117301.	3.3	2
117	GaN Schottky Barrier Diodes with High-Resistivity Edge Termination Formed by Boron Implantation. Chinese Physics Letters, 2013, 30, 057303.	3.3	2
118	Polarization-independent split bullâ€™s eye antennas for infrared nano-photodetectors. Scientific Reports, 2016, 6, 39106.	3.3	2
119	Electrical Instability of Amorphous-Indium-Gallium-Zinc-Oxide Thin-Film Transistors under Ultraviolet Illumination. Chinese Physics Letters, 2016, 33, 038502.	3.3	2
120	Performance improvement of 4H-SiC PIN ultraviolet avalanche photodiodes with different intrinsic layer thicknesses*. Chinese Physics B, 2019, 28, 098503.	1.4	2
121	Si-based Multiband Terahertz Antennas. , 2019, , .		2
122	Effect of a Single Threading Dislocation on Electrical and Single Photon Detection Characteristics of 4H-SiC Ultraviolet Avalanche Photodiodes. Chinese Physics Letters, 2020, 37, 068502.	3.3	2
123	Strain-driven phase manipulation of In^{\pm} and In^{p} -Ga ₂ O ₃ by nanoepitaxial lateral overgrowth on embedded In^{\pm} -In ₂ O ₃ submicron dots. Applied Physics Letters, 2021, 119, .	3.3	2
124	4H-SiC In^{\pm} n-i-p Extreme Ultraviolet Detector With Gradient Doping-Induced Surface Junction. IEEE Electron Device Letters, 2022, 43, 906-909.	3.9	2
125	Light emission of 2D photonic crystal based on nanocrystal-Si/SiO ₂ superlattice structure. Proceedings of SPIE, 2010, , .	0.8	1
126	The Effect of Oxygen Partial Pressure during Active Layer Deposition on Bias Stability of a-InGaZnO TFTs. Chinese Physics Letters, 2015, 32, 077303.	3.3	1

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127	High sensitivity x-ray detectors based on 4H-SiC p-i-n structure with 80μm thick intrinsic layer. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2021, 39, .	1.2	1
128	Electrically tunable terahertz metamaterials with embedded large-area transparent thin-film transistor arrays. , 0, .		1
129	Development of p-i-n Radiation Detectors based on Semi-Insulating 4H-SiC Substrate via Dual-face ion implantation. Solid-State Electronics, 2021, 187, 108196.	1.4	1
130	Photoresponse enhancement in nanoscale Ge photodetector through split bull's eye shaped plasmonic antenna. , 2011, , .		0
131	Silicon photonic integrated circuits: from devices to integration. Proceedings of SPIE, 2011, , .	0.8	0
132	Lasers: Manipulable and Hybridized, Ultralowâ€Threshold Lasing in a Plasmonic Laser Using Elliptical InGaN/GaN Nanorods (Adv. Funct. Mater. 37/2017). Advanced Functional Materials, 2017, 27, .	14.9	0
133	Chiral Metamaterials: A Terahertz Controlledâ€NOT Gate Based on Asymmetric Rotation of Polarization in Chiral Metamaterials (Advanced Optical Materials 18/2017). Advanced Optical Materials, 2017, 5, .	7.3	0